

HF/VHF power MOS transistor

BLF177

FEATURES

- High power gain
- Low intermodulation distortion
- Easy power control
- Good thermal stability
- Withstands full load mismatch.

DESCRIPTION

Silicon N-channel enhancement mode vertical D-MOS transistor designed for industrial and military applications in the HF/VHF frequency range.

The transistor is encapsulated in a 4-lead, SOT121 flange envelope, with a ceramic cap. All leads are isolated from the flange.

A marking code, showing gate-source voltage (V_{GS}) information is provided for matched pair applications. Refer to the 'General' section for further information.

PIN CONFIGURATION

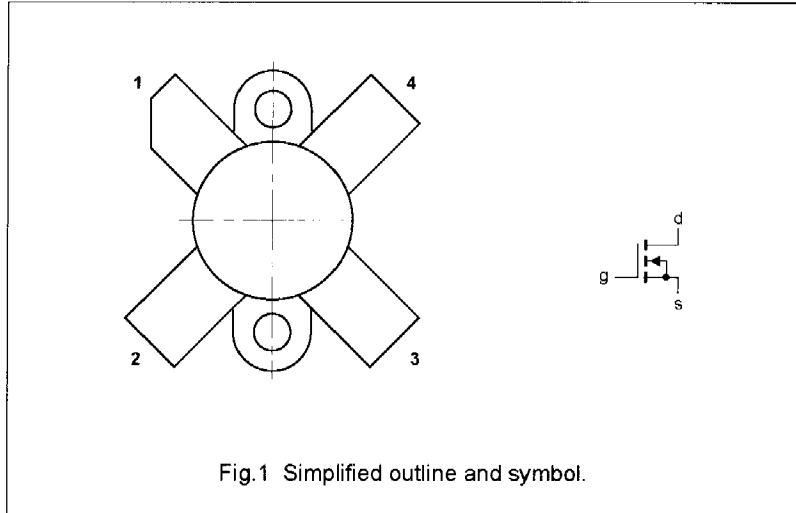


Fig.1 Simplified outline and symbol.

CAUTION

The device is supplied in an antistatic package. The gate-source input must be protected against static charge during transport and handling.

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

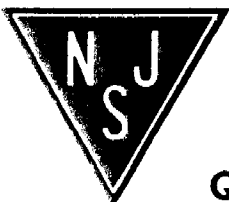
PINNING - SOT121

PIN	DESCRIPTION
1	drain
2	source
3	gate
4	source

QUICK REFERENCE DATA

RF performance at $T_H = 25^\circ\text{C}$ in a common source test circuit.

MODE OF OPERATION	f (MHz)	V_{DS} (V)	PL (W)	G_P (dB)	η_D (%)	d_3 (dB)	d_5 (dB)
SSB class-AB	28	50	150 (PEP)	> 20	> 35	< -30	< -30
CW class-B	108	50	150	typ. 19	typ. 70	-	-



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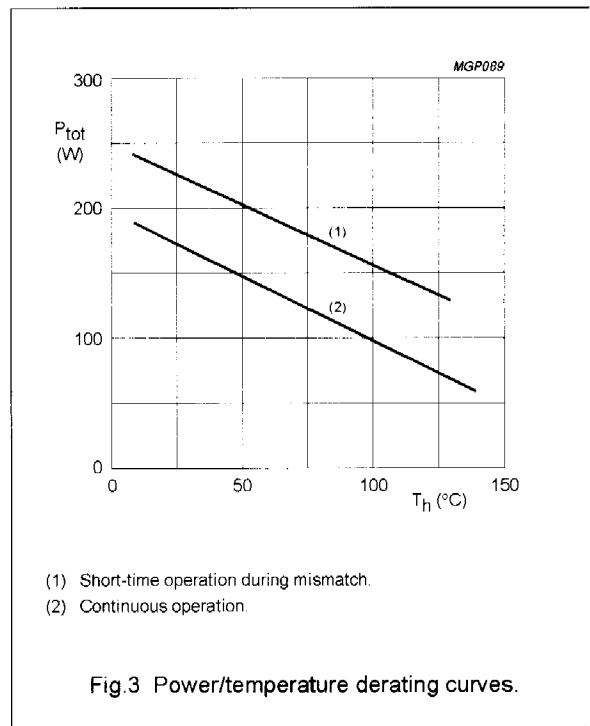
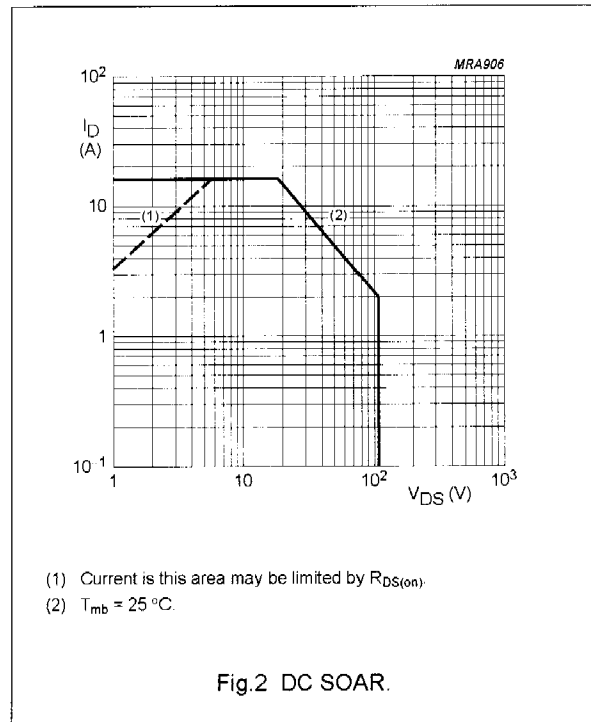
LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	110	V
$\pm V_{GS}$	gate-source voltage		–	20	V
I_D	DC drain current		–	16	A
P_{tot}	total power dissipation	up to $T_{mb} = 25\text{ }^\circ\text{C}$	–	220	W
T_{stg}	storage temperature		–65	150	$^\circ\text{C}$
T_j	junction temperature		–	200	$^\circ\text{C}$

THERMAL RESISTANCE

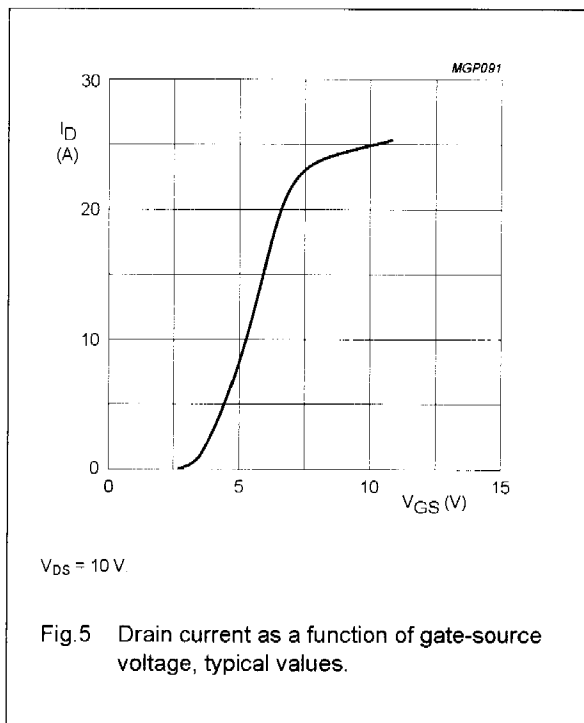
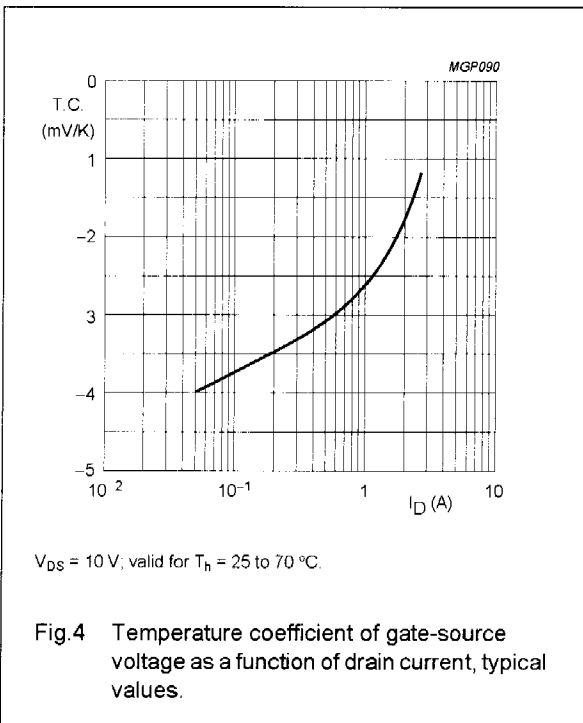
SYMBOL	PARAMETER	THERMAL RESISTANCE
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	max. 0.8 K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink	max. 0.2 K/W



CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 50\text{ mA}; V_{GS} = 0$	110	-	-	V
I_{DSS}	drain-source leakage current	$V_{GS} = 0; V_{DS} = 50\text{ V}$	-	-	2.5	mA
I_{GSS}	gate-source leakage current	$\pm V_{GS} = 20\text{ V}; V_{DS} = 0$	-	-	1	μA
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 50\text{ mA}; V_{DS} = 10\text{ V}$	2	-	4.5	V
ΔV_{GS}	gate-source voltage difference of matched pairs	$I_D = 50\text{ mA}; V_{DS} = 10\text{ V}$	-	-	100	mV
g_{fs}	forward transconductance	$I_D = 5\text{ A}; V_{DS} = 10\text{ V}$	4.5	6.2	-	S
$R_{DS(on)}$	drain-source on-state resistance	$I_D = 5\text{ A}; V_{GS} = 10\text{ V}$	-	0.2	0.3	Ω
I_{DSX}	on-state drain current	$V_{GS} = 10\text{ V}; V_{DS} = 10\text{ V}$	-	25	-	A
C_{is}	input capacitance	$V_{GS} = 0; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	480	-	pF
C_{os}	output capacitance	$V_{GS} = 0; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	190	-	pF
C_{rs}	feedback capacitance	$V_{GS} = 0; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	14	-	pF



PACKAGE OUTLINE

Flanged ceramic package; 2 mounting holes; 4 leads

SOT121B

